

FGC6000AX-120DS

HIGH POWER INVERTER USE
PRESS PACK TYPE

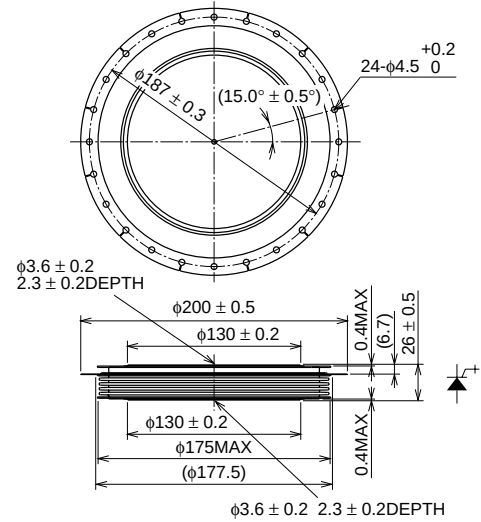
FGC6000AX-120DS



- ITQRM Repetitive controllable on-state current 6000A
- IT(AV) Average on-state current 2000A
- VDRM Repetitive peak off-state voltage 6000V
- Anode short type

OUTLINE DRAWING

Dimensions in mm



APPLICATION

Inverters, DC choppers, Induction heaters, DC to DC converters.

MAXIMUM RATINGS

Symbol	Parameter	Voltage class	Unit
VRRM	Repetitive peak reverse voltage	22	V
VSRM	Non-repetitive peak reverse voltage	22	V
VR(DC)	DC reverse voltage	22	V
VDRM	Repetitive peak off-state voltage*	6000	V
VDSM	Non-repetitive peak off-state voltage*	6000	V
VD(DC)	DC off-state voltage*	4800	V
VLDS	Long term DC stability voltage*	3200	V

* : VGK = -2V

Symbol	Parameter	Conditions	Ratings	Unit
ITQRM	Repetitive controllable on-state current	VDM = 5500V, VD = 3000V, LC = 0.3μH, VRG = 20V diGQ/dt = 10000A/μs, Tj = 25/125°C (see Fig. 1, 2)	6000	A
IT(RMS)	RMS on-state current	Applied for all conduction angles	3100	A
IT(AV)	Average on-state current	f = 60Hz, sinewave θ = 180°, Tf = 72°C	2000	A
ITSM	Surge on-state current	One half cycle at 60Hz, Tj = 125°C	40	kA
i ² t	Current-squared, time integration		6.7 × 10 ⁶	A ² s
di/dt	Critical rate of rise of on-state current	IT = 6000A, VD = 3000V, IGM = 300A, Tj = 125°C diG/dt = 200A/μs (see Fig. 1, 2)	1000	A/μs
VFGM	Peak forward gate voltage		10	V
VRGM	Peak reverse gate voltage		22	V
IFGM	Peak forward gate current		1500	A
IRGM	Peak reverse gate current		6000	A
PFGM	Peak forward gate power dissipation		15	kW
PRGM	Peak reverse gate power dissipation		180	kW
PFG(AV)	Average forward gate power dissipation		300	W
PRG(AV)	Average reverse gate power dissipation		900	W
Tj	Junction temperature		-40 ~ +125	°C
Tstg	Storage temperature		-40 ~ +150	°C
—	Mounting force required	(Recommended value 108kN)	98 ~ 118	kN
—	Weight	Typical value	3700	g

FGC6000AX-120DS

HIGH POWER INVERTER USE
PRESS PACK TYPE

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V_{TM}	On-state voltage	$I_T = 6000A, T_J = 125^{\circ}C$	—	—	4.0	V
I_{RRM}	Repetitive peak reverse current	$V_{RM} = 22V, T_J = 125^{\circ}C$	—	—	100	mA
I_{DRM}	Repetitive peak off-state current	$V_D = 6000V, V_{GK} = -2V, T_J = 125^{\circ}C$	—	—	320	mA
I_{GRM}	Reverse gate current	$V_{RM} = 22V, T_J = 125^{\circ}C$	—	—	100	mA
dv/dt	Critical rate of rise of off-state voltage	$V_D = 3000V, V_{GK} = -2V, T_J = 125^{\circ}C$ (see Fig. 3)	3000	—	—	V/ μs
t_{gt}	Turn-on time	$V_D = 3000V, I_T = 6000A, I_{GM} = 300A, T_J = 125^{\circ}C$ $di/dt = 1000A/\mu s, diGQ/dt = 200A/\mu s$ (see Fig. 2)	—	—	5.0	μs
t_s	Storage time	$I_T = 6000A, V_D = 3000V, diGQ/dt = 10000A/\mu s, T_J = 125^{\circ}C, L_c = 0.3\mu H, V_{RG} = 20V$ (see Fig. 2)	—	—	3.0	μs
I_{GT}	Gate trigger current	DC METHOD : $V_D = 24V, R_L = 0.1\Omega, T_J = 25^{\circ}C$	—	—	8.0	A
V_{GT}	Gate trigger voltage		—	—	1.5	V
$R_{th(j-f)}$	Thermal resistance	Junction to fin	—	—	0.0044	$^{\circ}C/W$

Fig. 1 Turn-on and Turn-off waveform

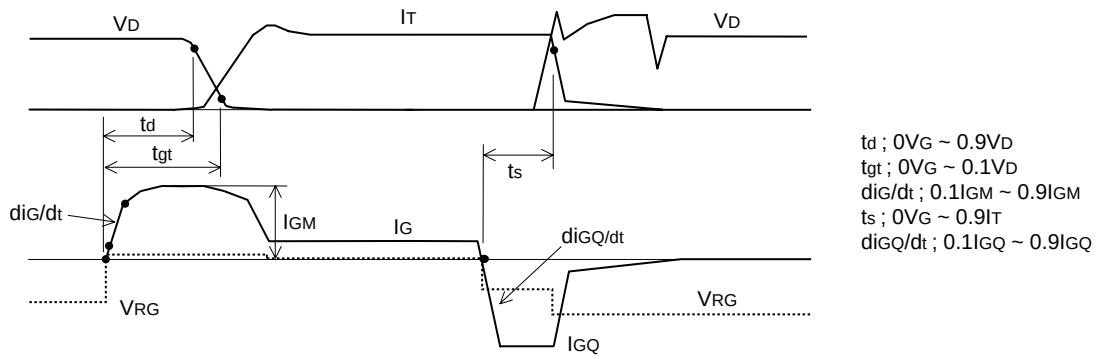


Fig. 2 Turn-on and Turn-off test circuit
(With clamp circuit)

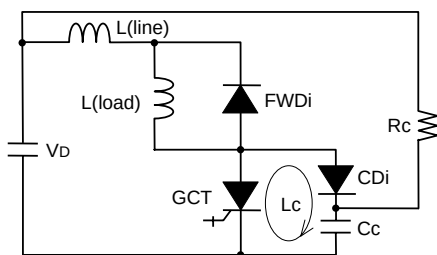


Fig. 3 dv/dt test waveform

